

$V_{DSM}$	=	5200 V
$I_{TAVM}$	=	2760 A
$I_{TRMS}$	=	4340 A
$I_{TSM}$	=	42000 A
$V_{T0}$	=	1.00 V
$r_T$	=	0.225 mW

## Phase Control Thyristor

# 5STP 25L5200

Doc. No. 5SYA1008-03 Aug.00

- Patented free-floating silicon technology
- Low on-state and switching losses
- Designed for traction, energy and industrial applications
- Optimum power handling capability
- Interdigitated amplifying gate.

### Blocking

Part Number	5STP 25L5200	5STP 25L5000	5STP 25L4600	Conditions
$V_{DSM}$ $V_{RSM}$	5200 V	5000 V	4600 V	$f = 5$ Hz, $t_p = 10$ ms
$V_{DRM}$ $V_{RRM}$	4400 V	4200 V	4000 V	$f = 50$ Hz, $t_p = 10$ ms
$V_{RSM1}$	5700 V	5500 V	5100 V	$t_p = 5$ ms, single pulse
$I_{DSM}$	$\leq 400$ mA			$V_{DSM}$
$I_{RSM}$	$\leq 400$ mA			$V_{RSM}$
$dV/dt_{crit}$	2000 V/ $\mu$ s			@ Exp. to $0.67 \times V_{DRM}$
$T_j = 125^\circ\text{C}$				

$V_{DRM}/V_{RRM}$  are equal to  $V_{DSM}/V_{RSM}$  values up to  $T_j = 110^\circ\text{C}$

### Mechanical data

$F_M$	Mounting force	nom.	70 kN
		min.	63 kN
		max.	84 kN
a	Acceleration		
	Device unclamped		50 m/s <sup>2</sup>
	Device clamped		100 m/s <sup>2</sup>
m	Weight		1.45 kg
$D_S$	Surface creepage distance		36 mm
$D_a$	Air strike distance		15 mm

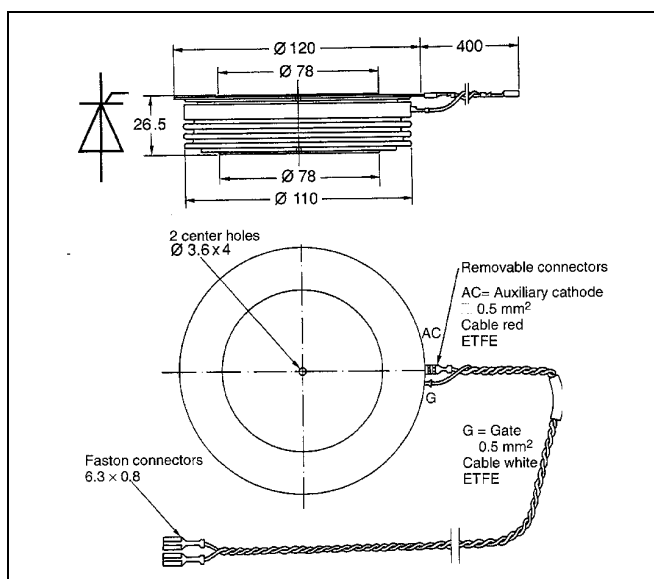


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## On-state

$I_{TAVM}$	Max. average on-state current	2760 A	Half sine wave, $T_C = 70^\circ\text{C}$	
$I_{TRMS}$	Max. RMS on-state current	4340 A		
$I_{TSM}$	Max. peak non-repetitive surge current	42000 A	$t_p = 10 \text{ ms}$	$T_j = 125^\circ\text{C}$ After surge: $V_D = V_R = 0\text{V}$
		45000 A	$t_p = 8.3 \text{ ms}$	
$I^2t$	Limiting load integral	8820 $\text{kA}^2\text{s}$	$t_p = 10 \text{ ms}$	
		8404 $\text{kA}^2\text{s}$	$t_p = 8.3 \text{ ms}$	
$V_T$	On-state voltage	1.70 V	$I_T = 3000 \text{ A}$	$T_j = 125^\circ\text{C}$
$V_{TO}$	Threshold voltage	1.00 V	$I_T = 1300 - 4000 \text{ A}$	
$r_T$	Slope resistance	0.225 $\text{m}\Omega$		
$I_H$	Holding current	50-125 mA	$T_j = 25^\circ\text{C}$	
		15-60 mA	$T_j = 125^\circ\text{C}$	
$I_L$	Latching current	100-500 mA	$T_j = 25^\circ\text{C}$	
		75-250 mA	$T_j = 125^\circ\text{C}$	

## Switching

$di/dt_{crit}$	Critical rate of rise of on-state current	250 $\text{A}/\mu\text{s}$	Cont.	$V_D \leq 0.67 \cdot V_{DRM}$ $T_j = 125^\circ\text{C}$ $I_{TRM} = 3000 \text{ A}$ $f = 50 \text{ Hz}$ $I_{FG} = 2.0 \text{ A}$ $t_r = 0.5 \mu\text{s}$
		500 $\text{A}/\mu\text{s}$	60 sec.	
$t_d$	Delay time	$\leq 3.0 \mu\text{s}$	$V_D = 0.4 \cdot V_{DRM}$	$I_{FG} = 2.0 \text{ A}$ $t_r = 0.5 \mu\text{s}$
$t_q$	Turn-off time	$\leq 700 \mu\text{s}$	$V_D \leq 0.67 \cdot V_{DRM}$ $dv_D/dt = 20\text{V}/\mu\text{s}$	$I_{TRM} = 3000 \text{ A}$ $T_j = 125^\circ\text{C}$ $V_R > 200 \text{ V}$
$Q_{rr}$	Recovery charge	min	5500 $\mu\text{As}$	$di_T/dt = -5 \text{ A}/\mu\text{s}$
		max	7500 $\mu\text{As}$	

## Triggering

$V_{GT}$	Gate trigger voltage	2.6 V	$T_j = 25^\circ\text{C}$
$I_{GT}$	Gate trigger current	400 mA	$T_j = 25^\circ\text{C}$
$V_{GD}$	Gate non-trigger voltage	0.3 V	$V_D = 0.4 \cdot V_{DRM}$
$I_{GD}$	Gate non-trigger current	10 mA	$V_D = 0.4 \cdot V_{DRM}$
$V_{FGM}$	Peak forward gate voltage	12 V	
$I_{FGM}$	Peak forward gate current	10 A	
$V_{RGM}$	Peak reverse gate voltage	10 V	
$P_G$	Maximum gate power loss	3 W	

### Thermal

$T_{j\max}$	Max. junction temperature	125°C	
$T_{j\text{stg}}$	Storage temperature range	-40...150°C	
$R_{\text{thJC}}$	Thermal resistance junction to case	14 K/kW	Anode side cooled
		14 K/kW	Cathode side cooled
		7 K/kW	Double side cooled
$R_{\text{thCH}}$	Thermal resistance case to heat sink	3 K/kW	Single side cooled
		1.5 K/kW	Double side cooled

Analytical function for transient thermal impedance:

$$Z_{\text{thJC}}(t) = \sum_{i=1}^n R_i(1 - e^{-t/\tau_i})$$

$i$	1	2	3	4
$R_i(\text{K/kW})$	4.7	0.853	1.07	0.49
$\tau_i(\text{s})$	0.4787	0.0824	0.0104	0.0041

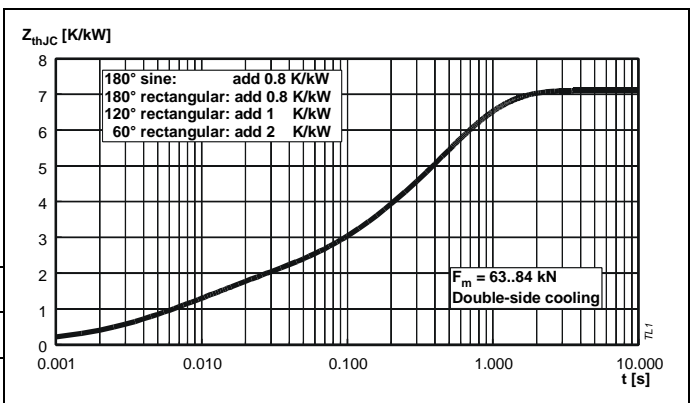


Fig. 1 Transient thermal impedance junction to case.

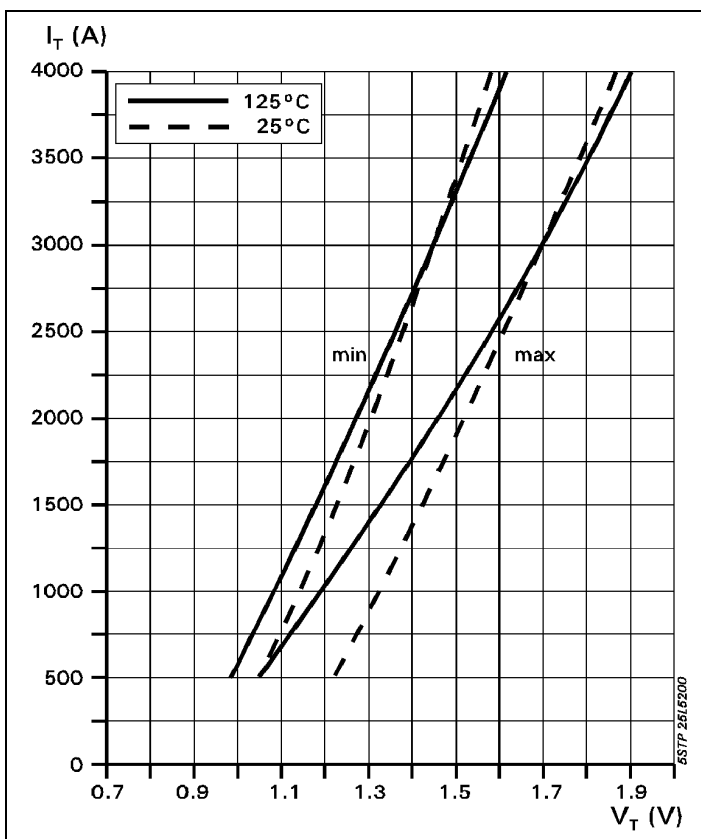


Fig 2. On-state characteristics.

On-state characteristic model:

$$V_T = A + B \cdot i_T + C \cdot \ln(i_T + 1) + D \cdot \sqrt{i_T}$$

Valid for  $i_T = 500 - 10000 \text{ A}$

A	B	C	D
-0.006184	0.00022	0.173291	-0.006405

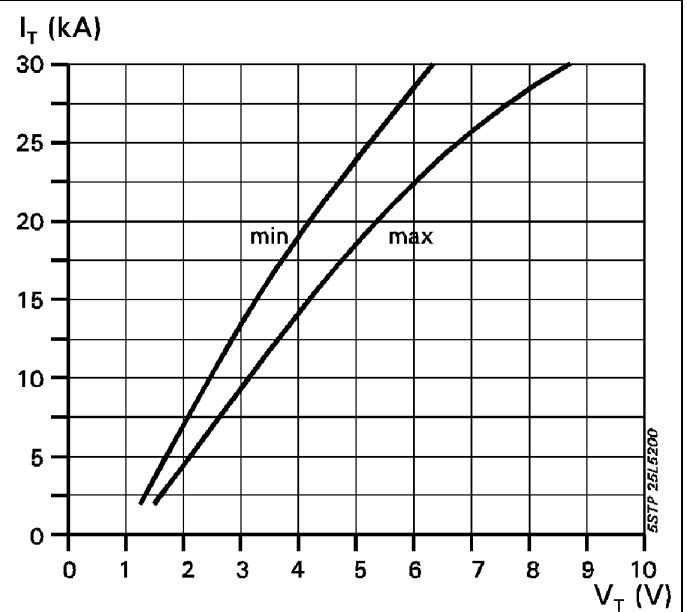
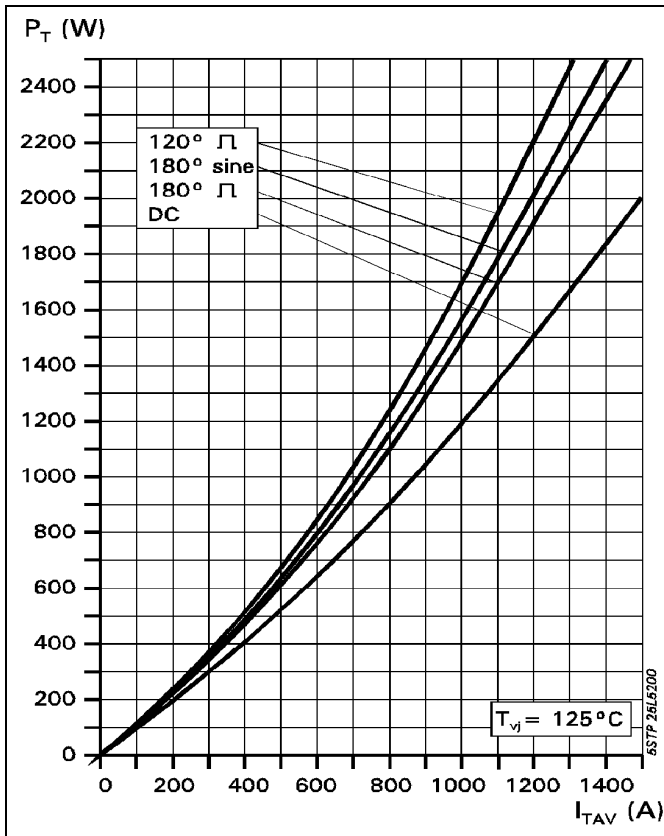
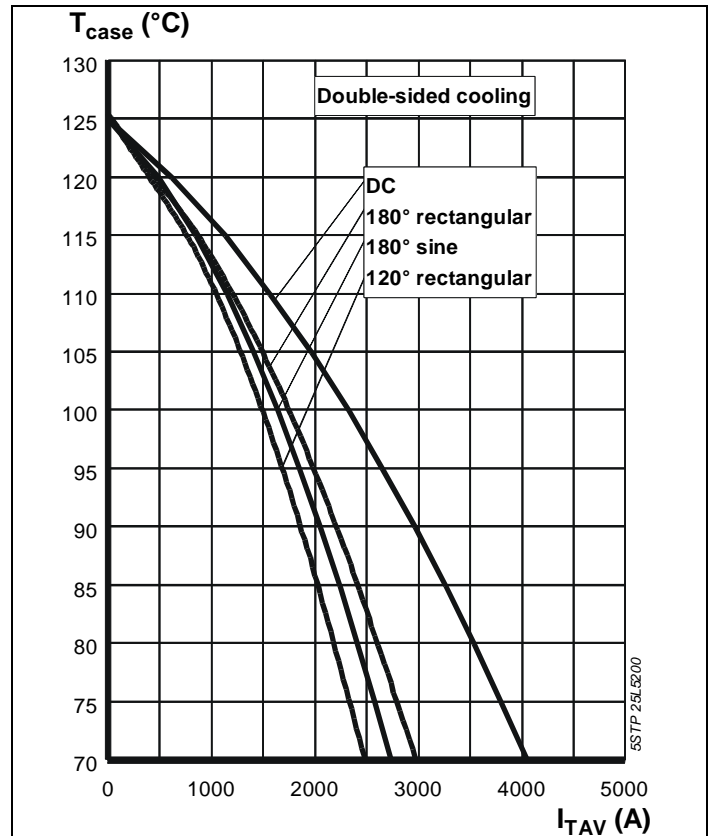


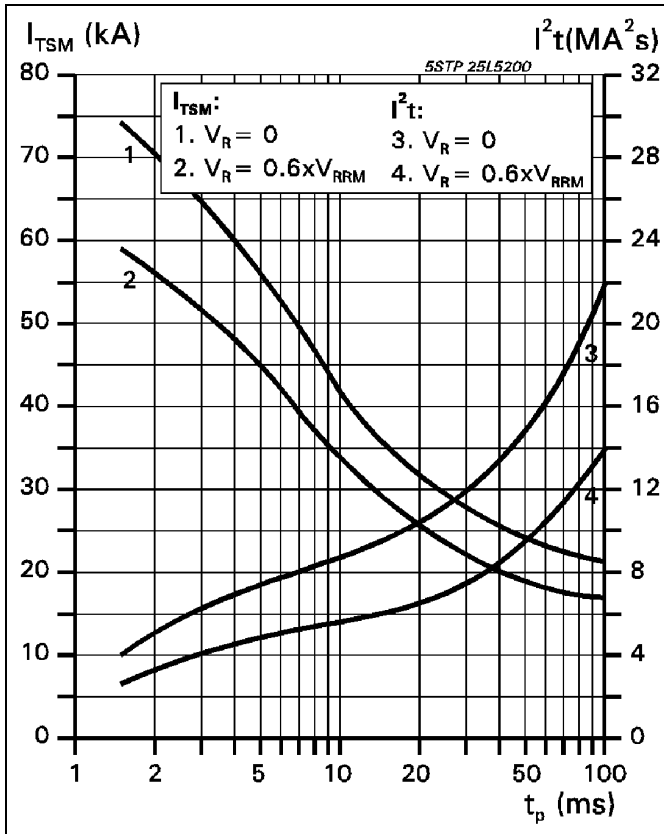
Fig. 3 On state characteristics.



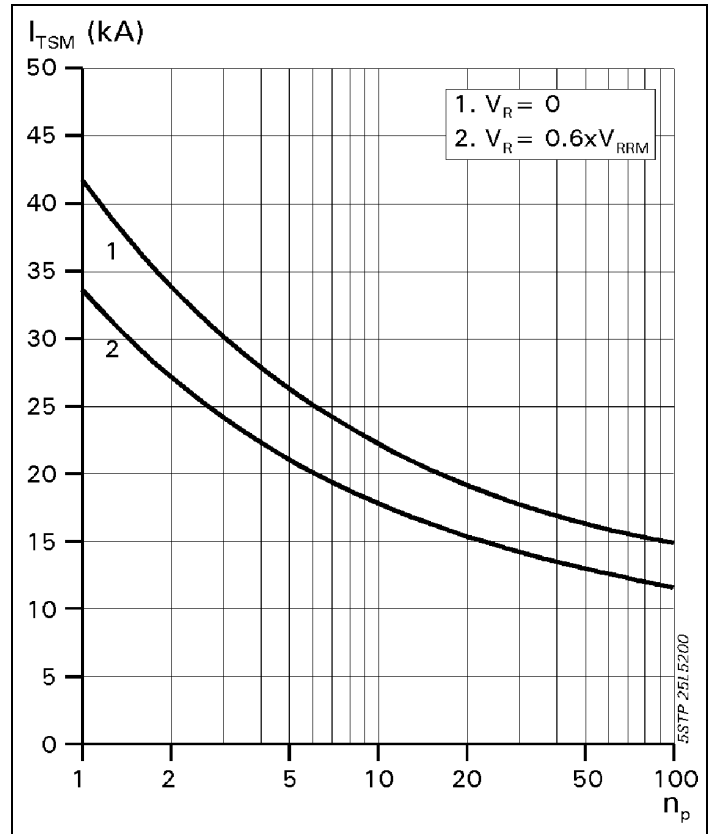
**Fig. 4** On-state power dissipation vs. mean on-state current. Turn-on losses excluded.



**Fig. 5** Max. permissible case temperature vs. mean on-state current.



**Fig. 6** Surge on-state current vs. pulse length. Half-sine wave.



**Fig. 7** Surge on-state current vs. number of pulses. Half-sine wave, 10 ms, 50Hz.

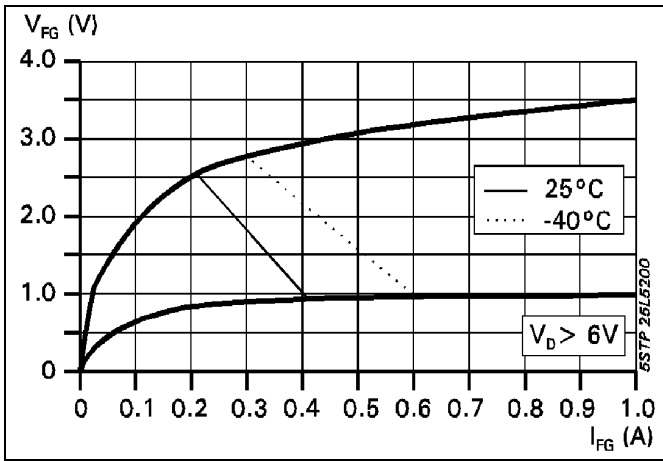


Fig. 8 Gate trigger characteristics.

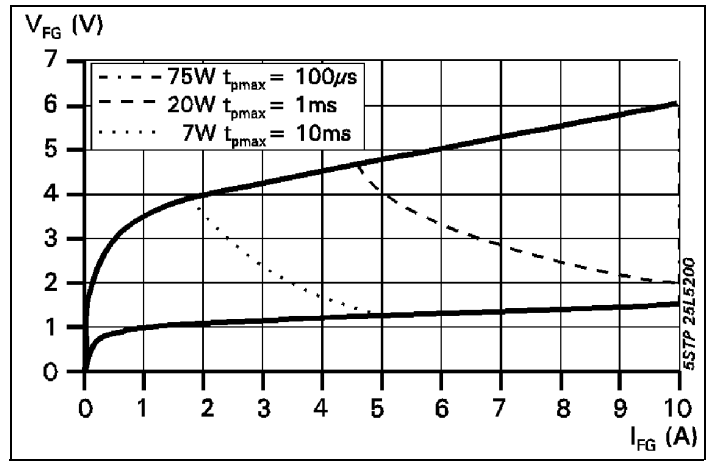


Fig. 9 Max. peak gate power loss.

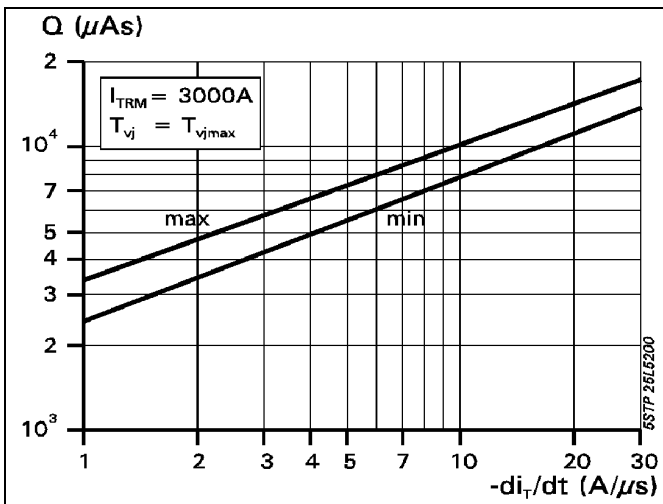


Fig. 10 Recovery charge vs. decay rate of on-state current.

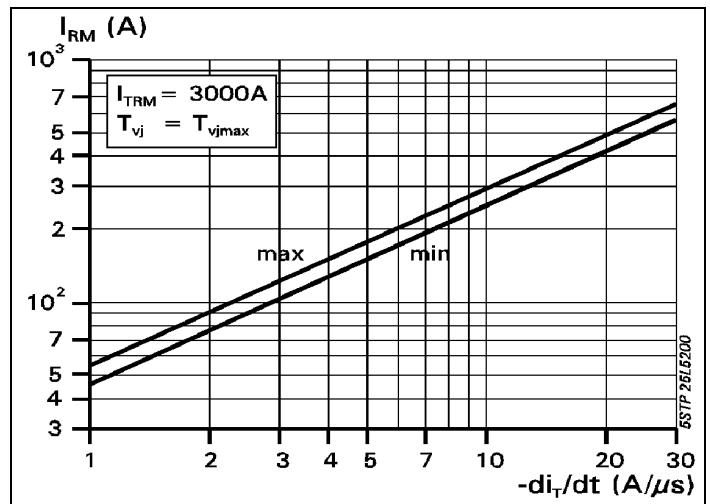


Fig. 11 Peak reverse recovery current vs. decay rate of on-state current.

Turn –off time, typical parameter relationship.

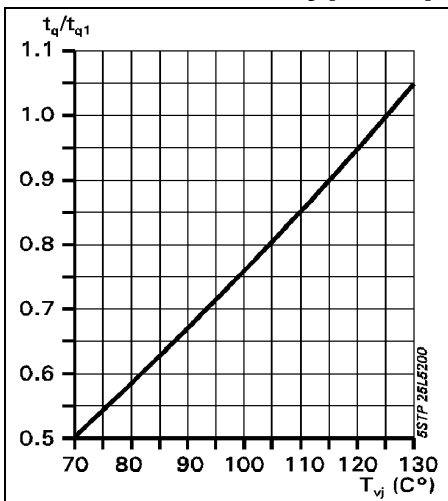


Fig. 12  $t_q/t_{q1} = f_1(T_j)$

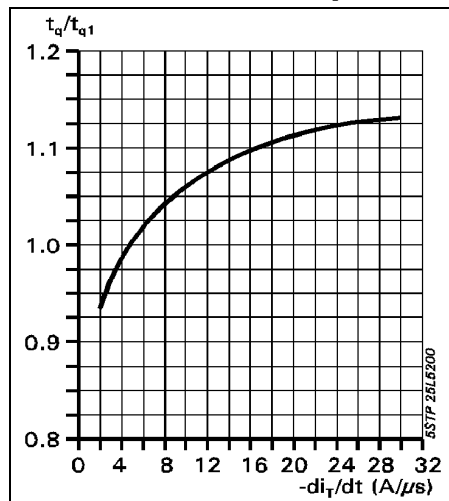


Fig. 13  $t_q/t_{q1} = f_2(-di/dt)$

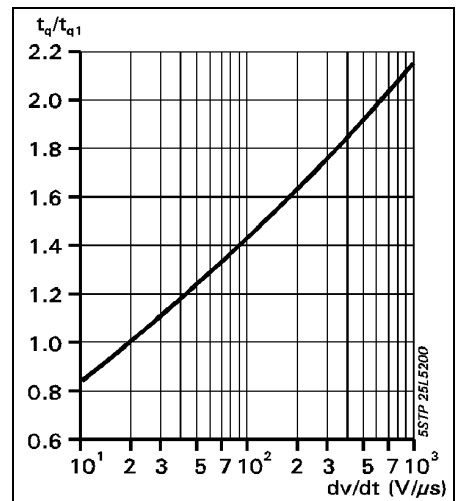
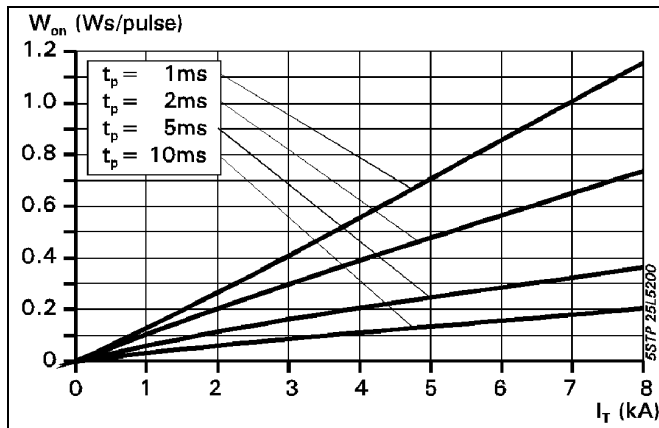


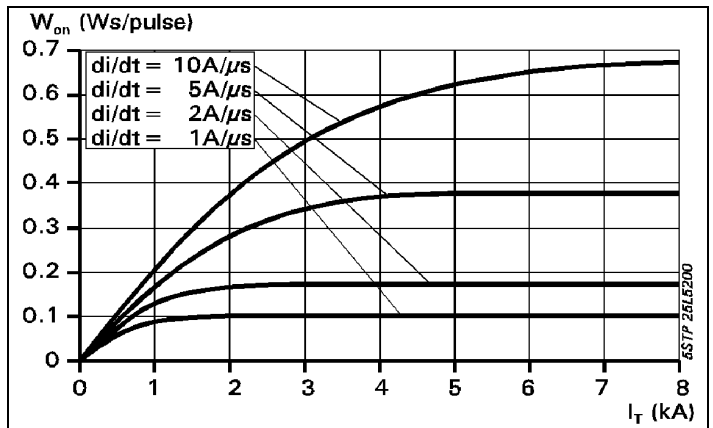
Fig. 14  $t_q/t_{q1} = f_3(dv/dt)$

$t_q = t_{q1} \cdot t_q/t_{q1} f_1(T_j) \cdot t_q/t_{q1} f_2(-di/dt) \cdot t_q/t_{q1} f_3(dv/dt)$   
 $t_{q1}$  : at normalized values (see page 2)  
 $t_q$  : at varying conditions

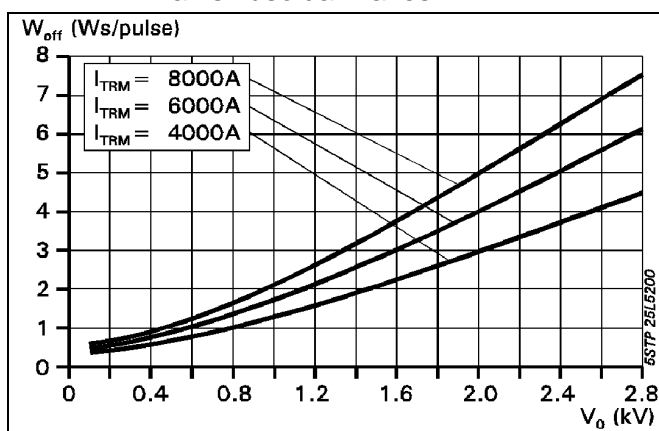
### Turn-on and Turn-off losses



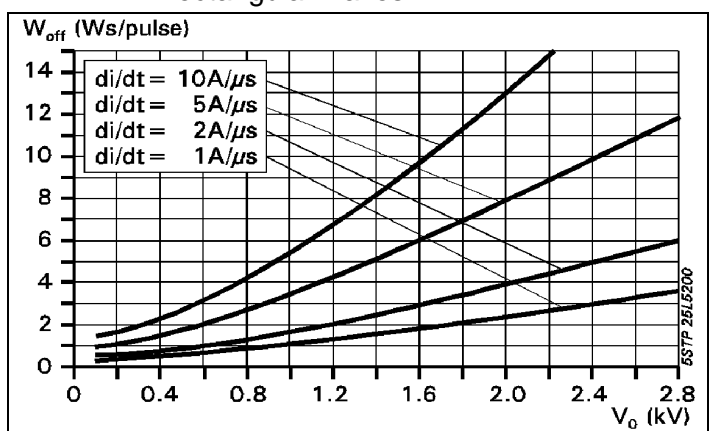
**Fig. 15**  $W_{on} = f(I_T, t_p)$ ,  $T_j = 125^\circ\text{C}$ .  
Half sinusoidal waves.



**Fig. 16**  $W_{on} = f(I_T, di/dt)$ ,  $T_j = 125^\circ\text{C}$ .  
Rectangular waves.



**Fig. 17**  $W_{off} = f(V_o, I_T)$ ,  $T_j = 125^\circ\text{C}$ .  
Half sinusoidal waves.  $t_p = 10$  ms.



**Fig. 18**  $W_{off} = f(V_o, di/dt)$ ,  $T_j = 125^\circ\text{C}$ .  
Rectangular waves.

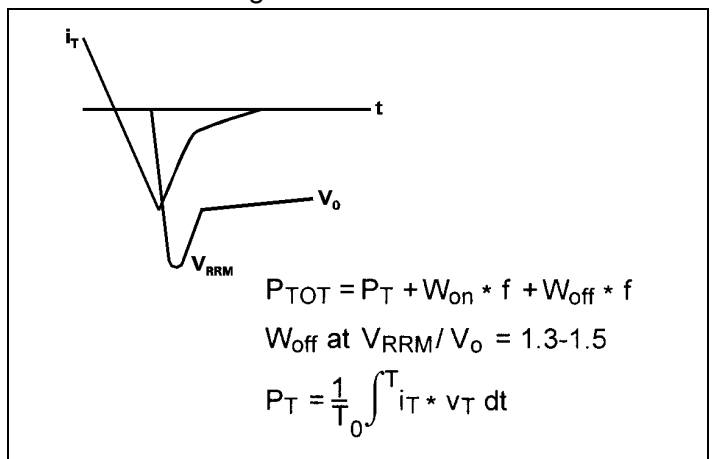


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**ABB Semiconductors AG**  
 Fabrikstrasse 3  
 CH-5600 Lenzburg, Switzerland

Telephone +41 (0)62 888 6419  
 Fax +41 (0)62 888 6306  
 Email Info@ch.abb.com  
 Internet www.abbsem.com